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(54) Title: METHOD FOR TEXTURING SILICON SURFACES AND WAFERS THEREOF

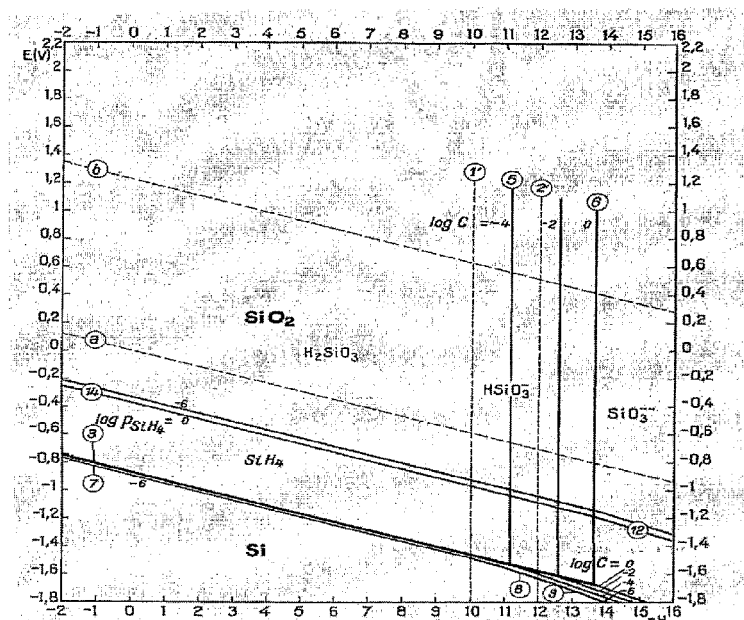


Figure 1: Pourbaix diagram of Si [1]

(57) Abstract: This invention relates to a method for texturing a silicon surface and silicon wafers made by the method, where the method comprises immersing the wafers in an alkaline solution at pH > 10, and applying a potential difference between the wafer and a platinum electrode in the electrolyte in the range of + 10 to + 85 V.

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